



## Standard Rectifier

$$V_{RRM} = 1600 \text{ V}$$

$$I_{FAV} = 80 \text{ A}$$

$$V_F = 1.55 \text{ V}$$

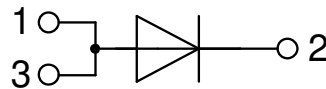
## Single Diode

### Part number

**DMA80IM1600HB**



Backside: cathode



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour
- High commutation robustness
- High surge capability

### Applications:

- Diode for main rectification
- For single and three phase bridge configurations

### Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

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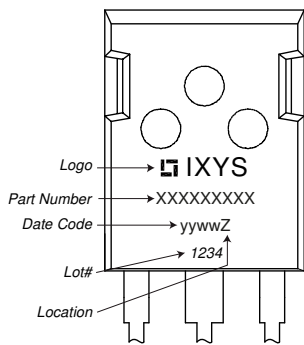


Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage				1700	V	
$V_{RRM}$	max. repetitive reverse blocking voltage				1600	V	
$I_R$	reverse current	$V_R = 1600\text{ V}$			40	$\mu\text{A}$	
		$V_R = 1600\text{ V}$			1.5	mA	
$V_F$	forward voltage drop	$I_F = 80\text{ A}$			1.17	V	
		$I_F = 160\text{ A}$			1.22	V	
		$I_F = 80\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.55	V
		$I_F = 160\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.59	V
$I_{FAV}$	average forward current	$T_C = 125^\circ\text{C}$ 180° sine			80	A	
$V_{F0}$	threshold voltage	} for power loss calculation only			0.82	V	
$r_F$	slope resistance				4.8	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				0.35	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W	
$P_{tot}$	total power dissipation				430	W	
$I_{FSM}$	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			1.30	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			1.41	kA
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			1.11	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			1.20	kA
$I^2t$	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			8.45	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			8.21	kA <sup>2</sup> s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			6.11	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			5.94	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		43	pF	



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

**Product Marking**



**Part description**

- D = Diode
- M = Standard Rectifier
- A = (up to 1800V)
- 80 = Current Rating [A]
- IM = Single Diode
- 1600 = Reverse Voltage [V]
- HB = TO-247AD (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA80IM1600HB	DMA80IM1600HB	Tube	30	505616

**Equivalent Circuits for Simulation**

*\* on die level*

$T_{VJ} = 175^{\circ}C$



**Rectifier**

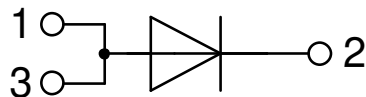
$V_{0\ max}$	threshold voltage	0.82	V
$R_{0\ max}$	slope resistance *	2.6	mΩ



**Outlines TO-247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212		5.38	
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



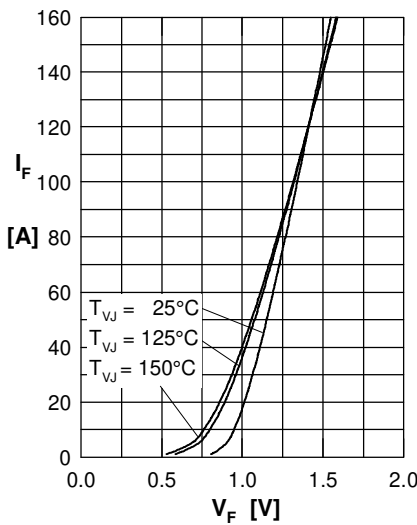
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

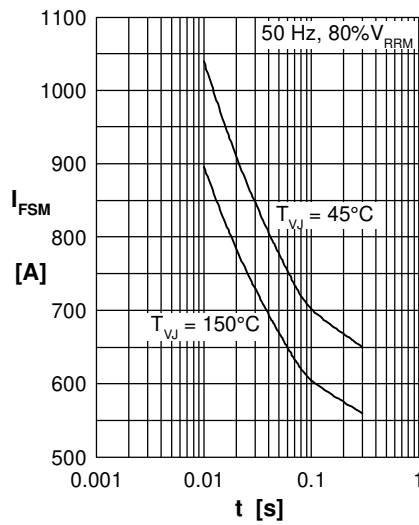


Fig. 2 Surge overload current versus time per diode

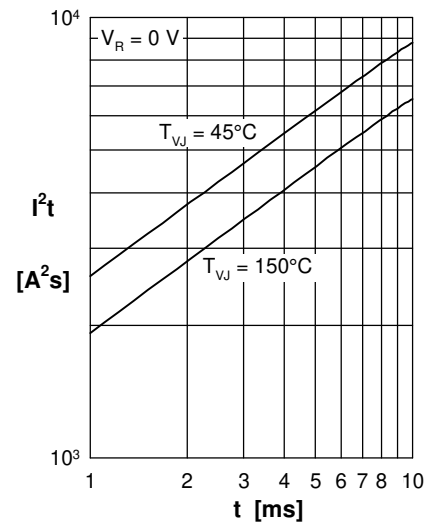
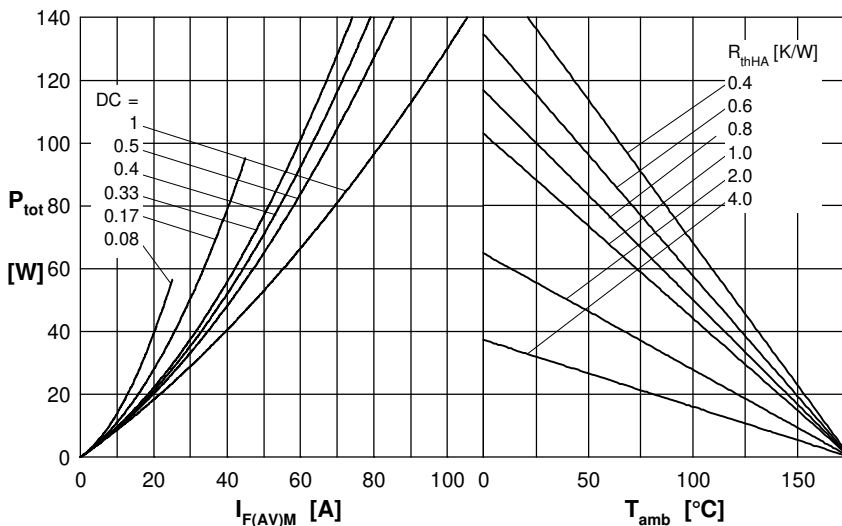

 Fig. 3  $I^2t$  versus time per diode


Fig. 4 Power dissipation versus direct output current and ambient temperature per diode

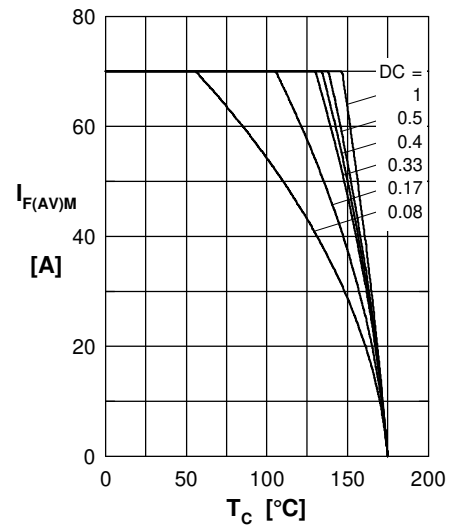


Fig. 5 Max. forward current versus case temperature per diode

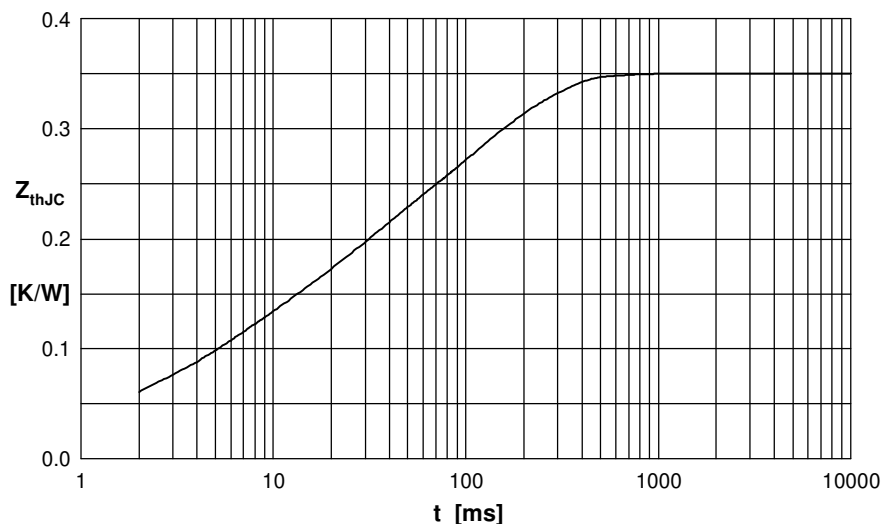


Fig. 6 Transient thermal impedance junction to case versus time per diode

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.023	0.0006
2	0.065	0.0038
3	0.094	0.0190
4	0.168	0.1300